



2SK4177 — N-Channel Silicon MOSFET

General-Purpose Switching Device Applications

Features

- Low ON-resistance, low input capacitance, ultrahigh-speed switching.
- Adoption of high reliability HVP process.
- Avalanche resistance guarantee.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	VDSS		1500	V
Gate-to-Source Voltage	VGSS		±20	V
Drain Current (DC)	ID		2	A
Drain Current (Pulse)	IDP	PW≤10μs, duty cycle≤1%	4	A
Allowable Power Dissipation	PD		1.65	W
		Tc=25°C	80	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C
Avalanche Energy (Single Pulse) *1	EAS		42	mJ
Avalanche Current *2	I _{AV}		2	A

*1 VDD=99V, L=20mH, IAV=2A

*2 L≤20mH, single pulse

Marking : K4177

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2SK4177

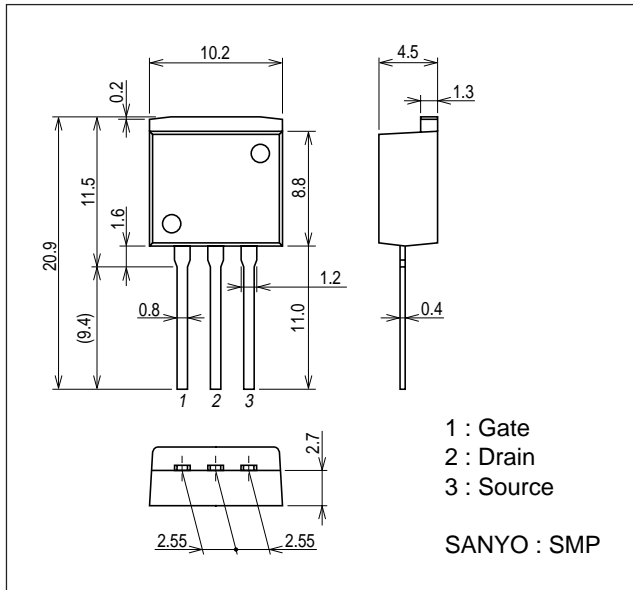
Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D=1mA, V_{GS}=0V$	1500			V
Zero-Gate Voltage Drain Current	I_{DSS}	$V_{DS}=1200V, V_{GS}=0V$			100	μA
Gate-to-Source Leakage Current	I_{GSS}	$V_{GS}=\pm 16V, V_{DS}=0V$			± 10	μA
Cutoff Voltage	$V_{GS(off)}$	$V_{DS}=10V, I_D=1mA$	2.5		3.5	V
Forward Transfer Admittance	$ y_{fs} $	$V_{DS}=20V, I_D=1A$	0.7	1.4		S
Static Drain-to-Source On-State Resistance	$R_{DS(on)}$	$I_D=1A, V_{GS}=10V$		10	13	Ω
Input Capacitance	C_{iss}	$V_{DS}=30V, f=1MHz$		380		pF
Output Capacitance	C_{oss}	$V_{DS}=30V, f=1MHz$		70		pF
Reverse Transfer Capacitance	C_{rss}	$V_{DS}=30V, f=1MHz$		40		pF
Turn-ON Delay Time	$t_{d(on)}$	See specified Test Circuit.		12		ns
Rise Time	t_r	See specified Test Circuit.		37		ns
Turn-OFF Delay Time	$t_{d(off)}$	See specified Test Circuit.		152		ns
Fall Time	t_f	See specified Test Circuit.		59		ns
Total Gate Charge	Q_g	$V_{DS}=200V, V_{GS}=10V, I_D=2A$		37.5		nC
Gate-to-Source Charge	Q_{gs}	$V_{DS}=200V, V_{GS}=10V, I_D=2A$		2.7		nC
Gate-to-Drain "Miller" Charge	Q_{gd}	$V_{DS}=200V, V_{GS}=10V, I_D=2A$		20		nC
Diode Forward Voltage	V_{SD}	$I_S=2A, V_{GS}=0V$		0.88	1.2	V

Note) Although the protection diode is contained between gate and source, be careful of handling enough.

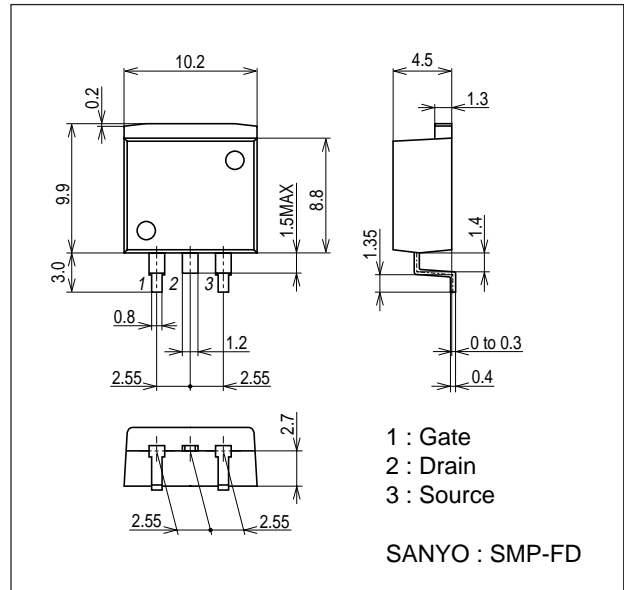
Package Dimensions

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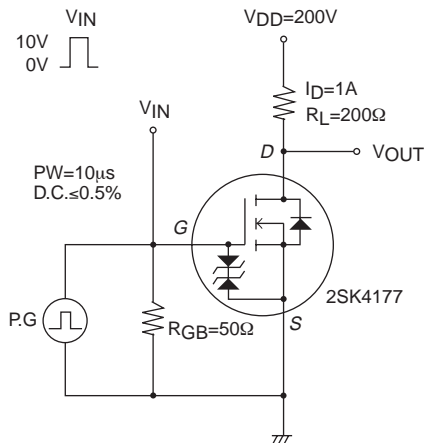


Package Dimensions

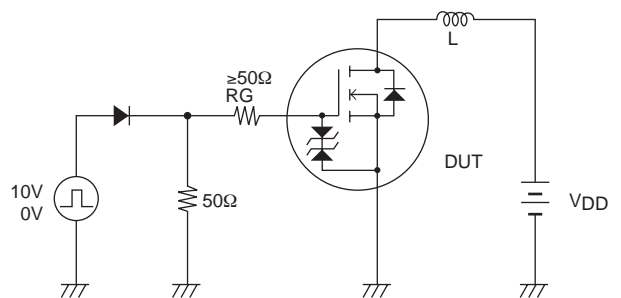
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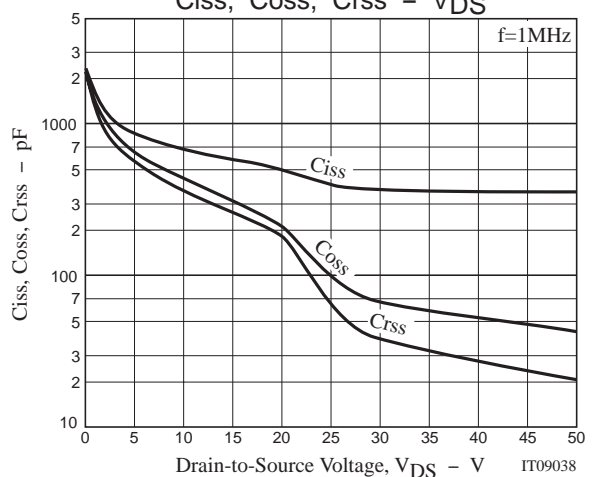
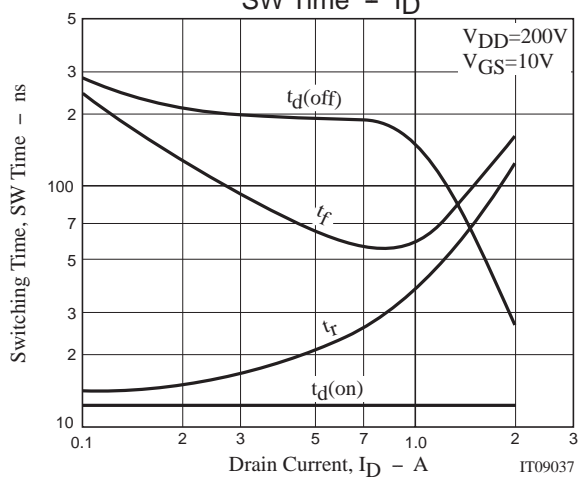
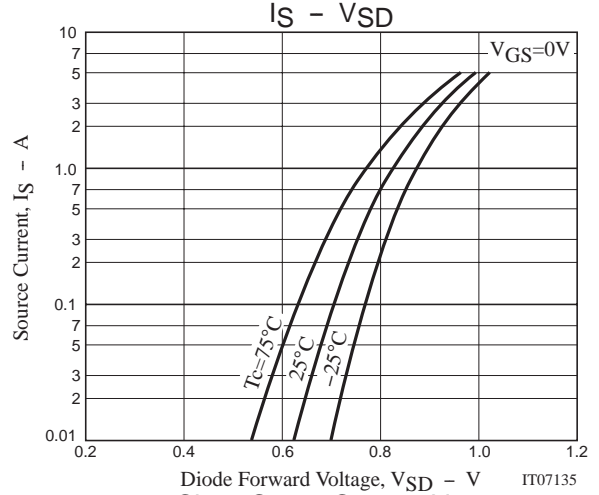
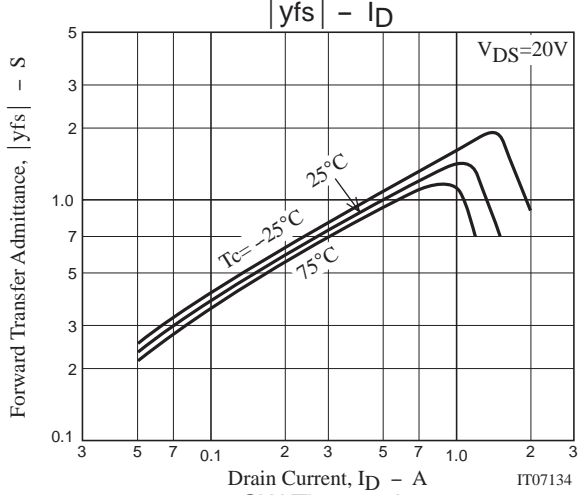
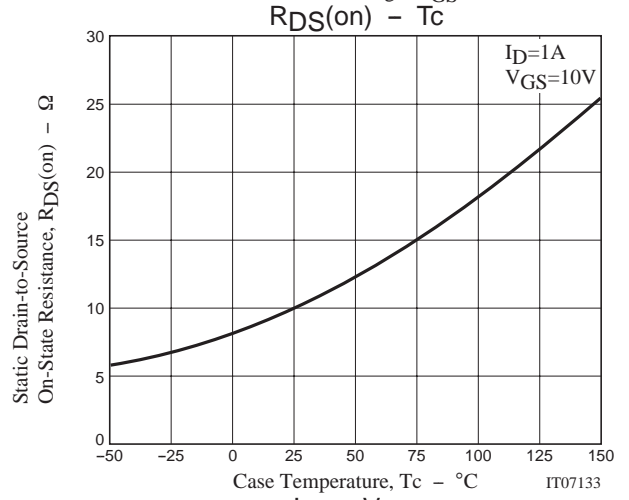
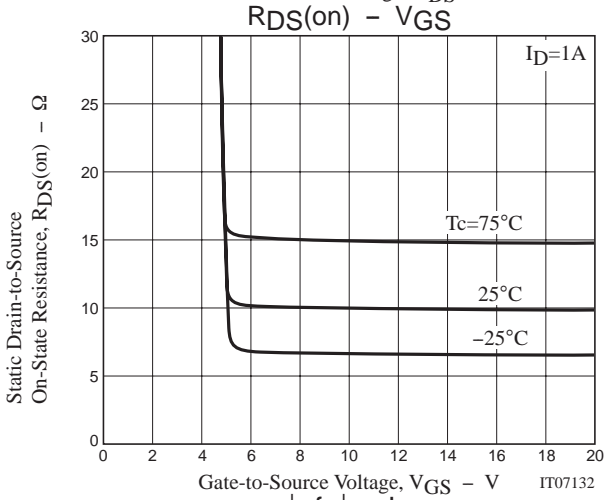
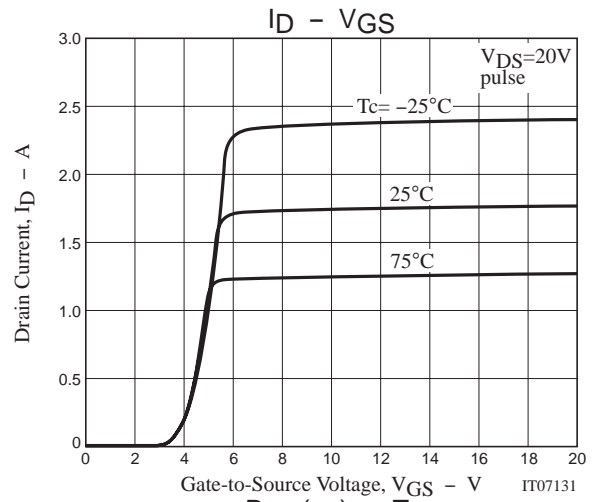
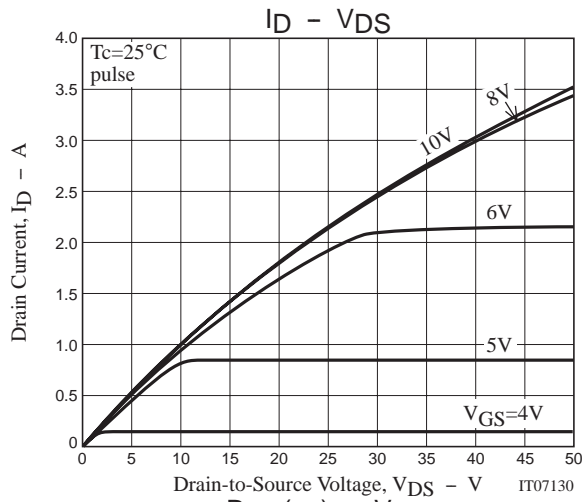


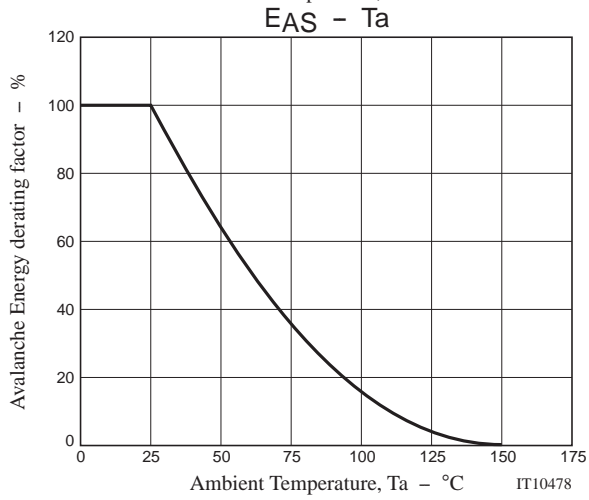
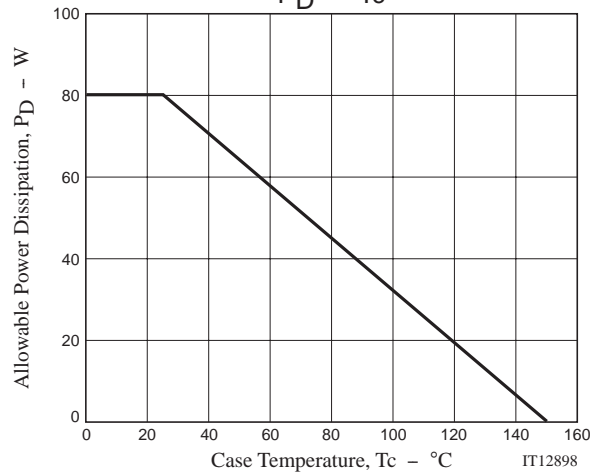
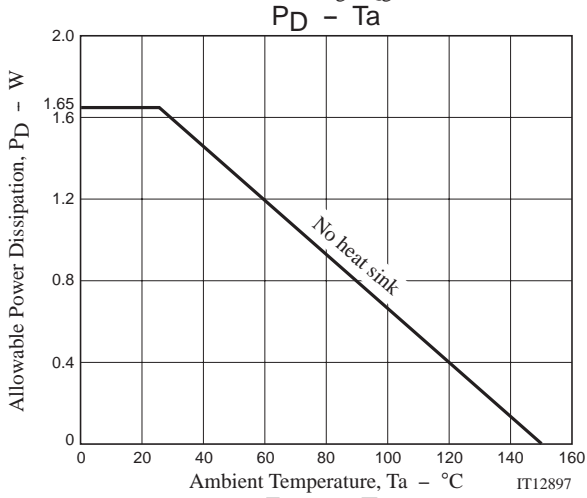
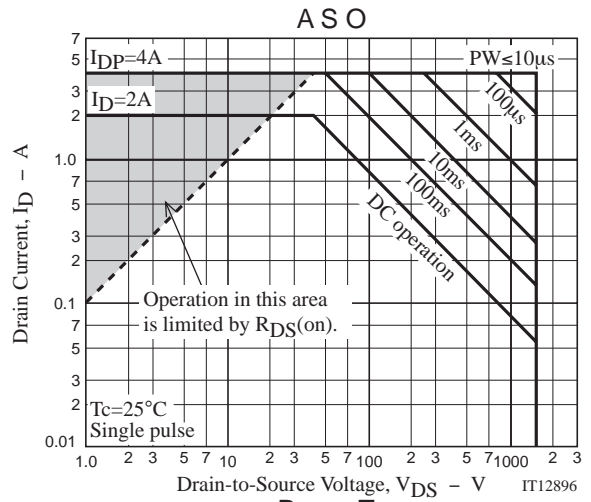
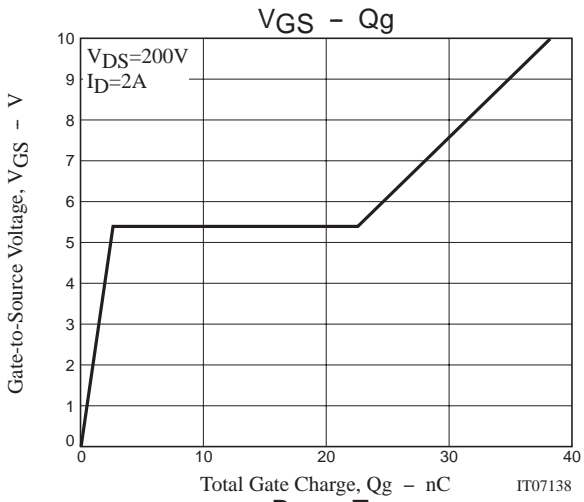
Switching Time Test Circuit



Avalanche Resistance Test Circuit







Note on usage : Since the 2SK4177 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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